

FDB8444TS

N-Channel PowerTrench[®] MOSFET with Temperature Sensor

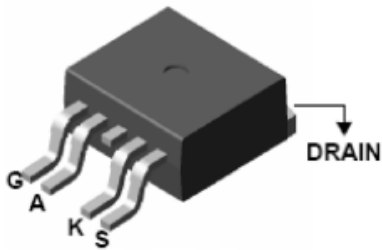
40V, 70A, 5mΩ

Features

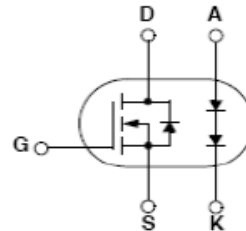
- Typ $r_{DS(on)}$ = 3.8mΩ at $V_{GS} = 10V$, $I_D = 70A$
- Typ $Q_{g(TOT)}$ = 130nC at $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems



TO263 5 LEADS



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current Continuous ($T_C = 140^\circ\text{C}$, $V_{GS} = 10\text{V}$)	70	A
	Continuous ($T_{amb} = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, with $R_{\theta JA} = 43^\circ\text{C/W}$)	20	
	Pulsed	See Figure 4	
E_{AS}	Single Pulse Avalanche Energy (Note 1)	439	mJ
P_D	Power Dissipation	181	W
	Derate above 25°C	1.2	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	0.83	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-263, 1in ² copper pad area	43	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB8444TS	FDB8444TS	TO-263 5LDS	330mm	24mm	800 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$T_C = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	2.8	4	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 70\text{A}$, $V_{GS} = 10\text{V}$	-	3.8	5	m Ω
		$I_D = 70\text{A}$, $V_{GS} = 10\text{V}$, $T_J = 175^\circ\text{C}$	-	6.5	8.5	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	8410	-	pF	
C_{oss}	Output Capacitance		-	765	-	pF	
C_{rss}	Reverse Transfer Capacitance		-	485	-	pF	
R_G	Gate Resistance	$f = 1\text{MHz}$	-	1.8	-	Ω	
$Q_{g(TOT)}$	Total Gate Charge at 20V	$V_{GS} = 0$ to 20V	$V_{DD} = 20\text{V}$ $I_D = 70\text{A}$	-	260	338	nC
$Q_{g(10)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V		-	130	169	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V		-	15.5	-	nC
Q_{gs}	Gate to Source Gate Charge			-	33	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau			-	17.7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	30	-	nC

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
t_{on}	Turn-On Time	$V_{DD} = 20\text{V}, I_D = 70\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 2\Omega$	-	-	96	ns
$t_{d(on)}$	Turn-On Delay Time		-	14.6	-	ns
t_r	Rise Time		-	19.1	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	44	-	ns
t_f	Fall Time		-	17.3	-	ns
t_{off}	Turn-Off Time		-	-	98	ns

Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 70\text{A}$	-	1.0	1.25	V
		$I_{SD} = 40\text{A}$	-	0.9	1.0	
t_{rr}	Reverse Recovery Time	$I_{SD} = 70\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	51	66	ns
Q_{rr}	Reverse Recovery Charge		-	70	91	nC

Temperature Sense Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_f	Temperature Sense Diode Voltage	$I_f = 1\text{mA}$	1.58	1.61	1.63	V
S_f	Temperature Sense Diode Temperature Coefficient	$I_f = 1\text{mA}, -55^\circ\text{C} < T_J < 175^\circ\text{C}$	-2.55	-2.74	-3.11	mV/ $^\circ\text{C}$

Notes:

1: Starting $T_J = 25^\circ\text{C}$, $L = 0.28\text{mH}$, $I_{AS} = 56\text{A}$.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>
 All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

Typical Characteristics

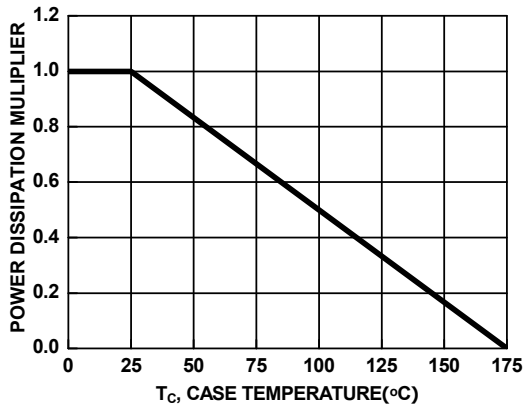


Figure 1. Normalized Power Dissipation vs Case Temperature

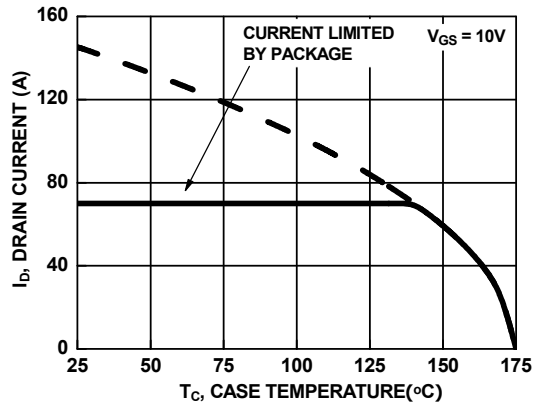


Figure 2. Maximum Continuous Drain Current vs Case Temperature

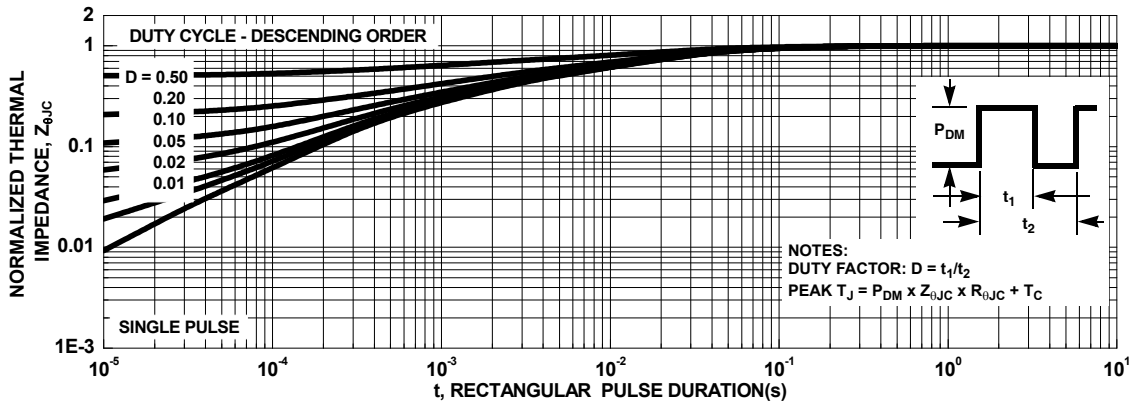


Figure 3. Normalized Maximum Transient Thermal Impedance

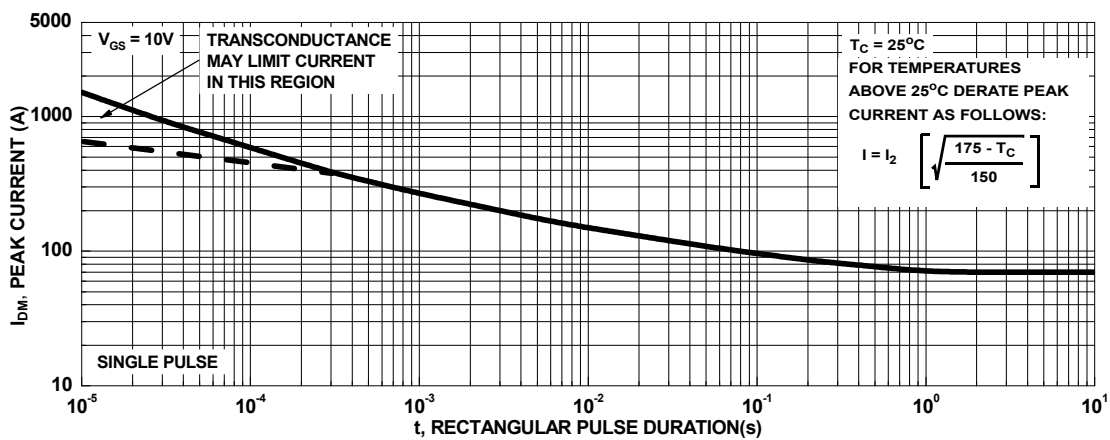


Figure 4. Peak Current Capability

Typical Characteristics

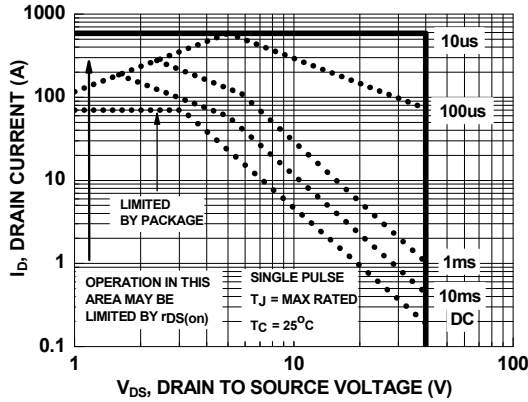
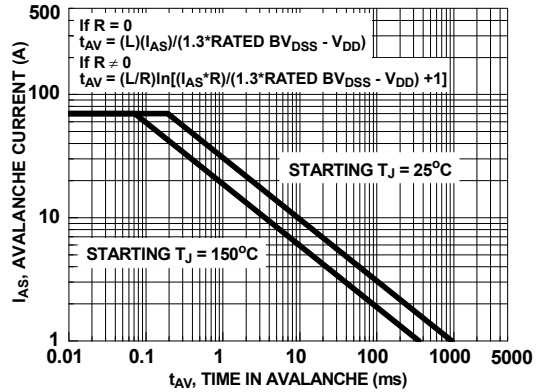


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515
 Figure 6. Unclamped Inductive Switching Capability

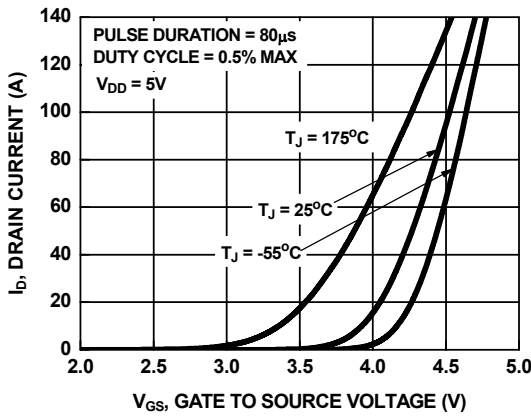


Figure 7. Transfer Characteristics

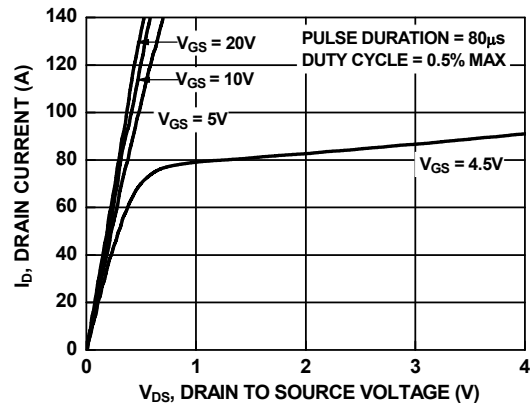


Figure 8. Saturation Characteristics

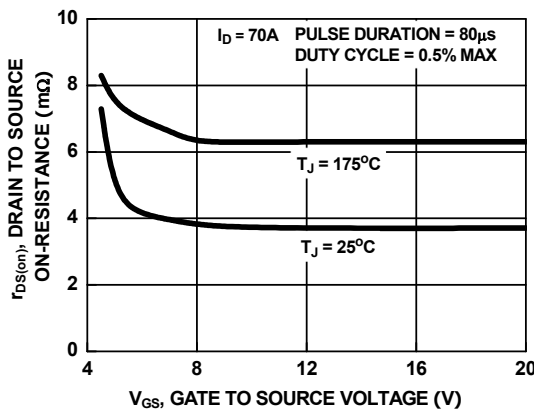


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

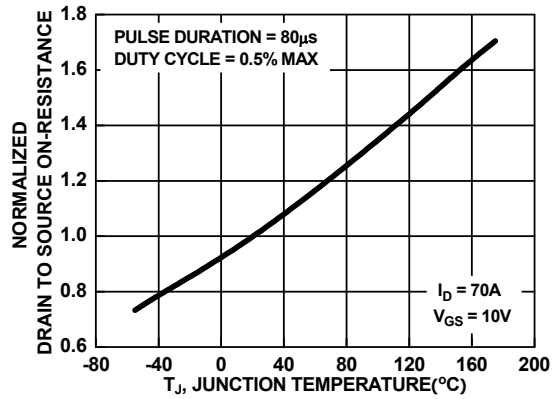


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

Typical Characteristics

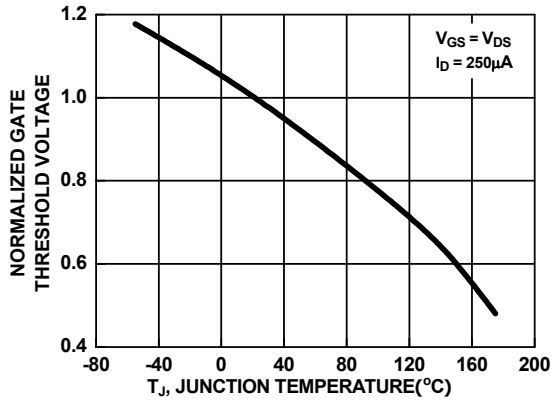


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

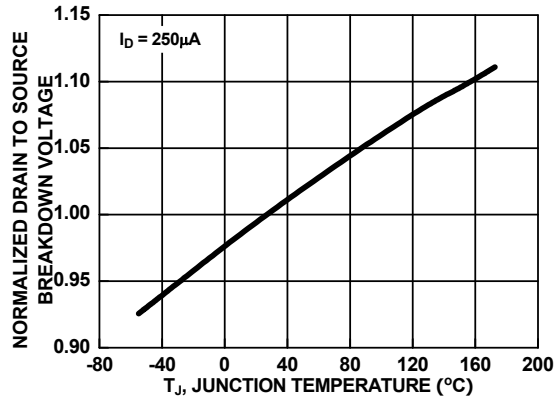


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

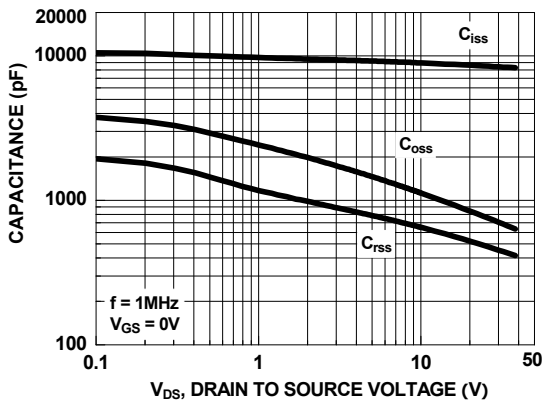


Figure 13. Capacitance vs Drain to Source Voltage

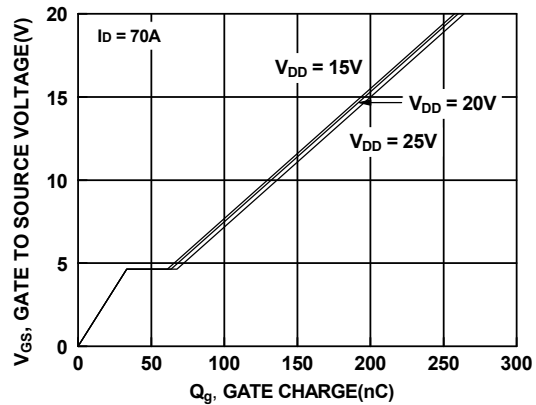


Figure 14. Gate Charge vs Gate to Source Voltage

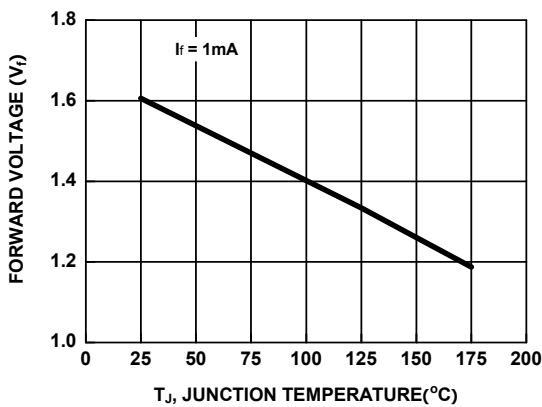



Figure 15. Temperature Sense Diode Forward Voltage vs. Junction Temperature



TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--------------------------------------|------------------------------------------------------------------------------------------------|----------------------------------------|----------------------------------|
| ACEx [®] | Green FPS [™] | Power247 [®] | SuperSOT [™] -8 |
| Build it Now [™] | Green FPS [™] e-Series [™] | POWEREDGE [®] | SyncFET [™] |
| CorePLUS [™] | GTO [™] | Power-SPM [™] | The Power Franchise [®] |
| CROSSVOLT [™] | i-Lo [™] | PowerTrench [®] | the power franchise |
| CTL [™] | IntelliMAX [™] | Programmable Active Droop [™] | TinyBoost [™] |
| Current Transfer Logic [™] | ISOPLANAR [™] | QFET [®] | TinyBuck [™] |
| EcoSPARK [®] | MegaBuck [™] | QS [™] | TinyLogic [®] |
| F [®] | MICROCOUPLER [™] | QT Optoelectronics [™] | TINYOPTO [™] |
| Fairchild [®] | MicroFET [™] | Quiet Series [™] | TinyPower [™] |
| Fairchild Semiconductor [®] | MicroPak [™] | RapidConfigure [™] | TinyPWM [™] |
| FACT Quiet Series [™] | MillerDrive [™] | SMART START [™] | TinyWire [™] |
| FACT [®] | Motion-SPM [™] | SPM [®] | μSerDes [™] |
| FAST [®] | OPTOLOGIC [®] | STEALTH [™] | UHC [®] |
| FastvCore [™] | OPTOPLANAR [®] | SuperFET [™] | UniFET [™] |
| FPS [™] |  [®] | SuperSOT [™] -3 | VCX [™] |
| FRFET [®] | PDP-SPM [™] | SuperSOT [™] -6 | |
| Global Power Resource SM | Power220 [®] | | |

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.